

## SM8T20A THRU SM8T43A TRANSIENT VOLTAGE SUPPRESSOR



### Features

- Junction passivation optimized design passivated anisotropic rectifier technology
- $T_J = 175^\circ\text{C}$  capability suitable for high reliability and automotive requirement.
- Available in uni-directional polarity only
- Low leakage current
- Low forward voltage drop
- High surge capability
- AEC-Q101 qualified.

### Circuit Diagram



### Mechanical Data

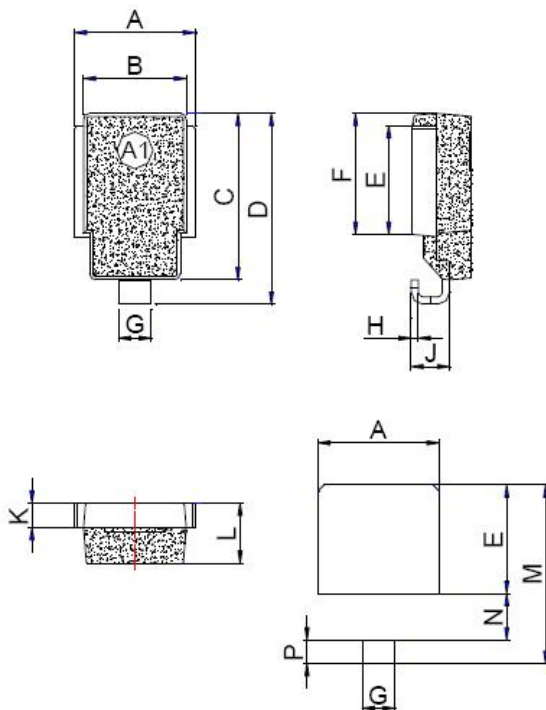
- Case: DO-218AB
- Molding compound meets UL 94V-0 flammability rating
- Base P/NHE3-RoHS-compliant, AEC-Q101 qualified
- Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

### Maximum Ratings and Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Peak pulse power dissipation on 10/1000 $\mu\text{s}$ waveform	$P_{PPM}$	8000	W
Peak pulse power dissipation on 10/10000 $\mu\text{s}$ waveform		6000	W
Power dissipation on infinite heat sink at $T_C = 25^\circ\text{C}$	$P_D$	8.5	W
Peak forward surge current 8.3 ms single half sine-wave	$I_{FSM}$	750	A
Typical thermal resistance, junction to case	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	$^\circ\text{C}$

**Electrical Characteristics@T<sub>A</sub>=25° C unless otherwise specified**

DEVICE TYPE	REVERSE STAND-OFF VOLTAGE V <sub>RWM</sub> (V)	BREAKDOWN VOLTAGE V <sub>BR</sub> (V) @I <sub>T</sub>		TEST CURRENT I <sub>T</sub>	CLAMPING VOLTAGE V <sub>C</sub> @I <sub>PP</sub>	PEAK PULSE CURRENT AT 10/1000μs WAVEFORM I <sub>PP</sub>	REVERSE LEAKAGE CURRENT I <sub>R</sub>	
		MIN.	MAX.	MA	V	A	μA@25°C	μA@175°C
SM8T20A	20	22.2	24.5	5	32.4	247	5	150
SM8T22A	22	24.4	26.9	5	35.5	225	5	150
SM8T24A	24	26.7	29.5	5	38.9	205	5	150
SM8T26A	26	28.9	31.9	5	42.1	190	5	150
SM8T28A	28	31.1	34.4	5	45.4	176	5	150
SM8T30A	30	33.3	36.8	5	48.4	165	5	150
SM8T32A	32	35.5	39.4	5	51.4	156	5	150
SM8T33A	33	36.7	40.6	5	53.3	150	5	150
SM8T36A	36	40.0	44.2	5	58.1	138	5	150
SM8T40A	40	44.4	49.1	5	64.5	124	5	150
SM8T43A	43	47.8	52.8	5	69.4	115	5	150

**Mechanical Dimensions DO-218AB(Inches/Millimeters)**


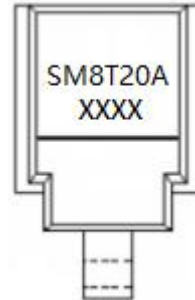
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	9.5	10.5	0.374	0.413
B	8.3	8.7	0.327	0.342
C	13.3	13.7	0.524	0.539
D	15.0	16.0	0.592	0.628
E	8.5	9.1	0.335	0.358
F	9.5	10.1	0.374	0.398
G	2.4	3.0	0.094	0.118
H	0.5	0.7	0.020	0.028
J	2.7	3.7	0.106	0.146
K	1.9	2.1	0.075	0.083
L	4.7	5.1	0.185	0.201
M	14.2	14.8	0.559	0.583
N	3.5	4.1	0.138	0.161
P	1.6	2.2	0.063	0.087

**Ordering Information**

Device	Package	Shipping
SM8T20A THRU SM8T43A	DO-218AB	750pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

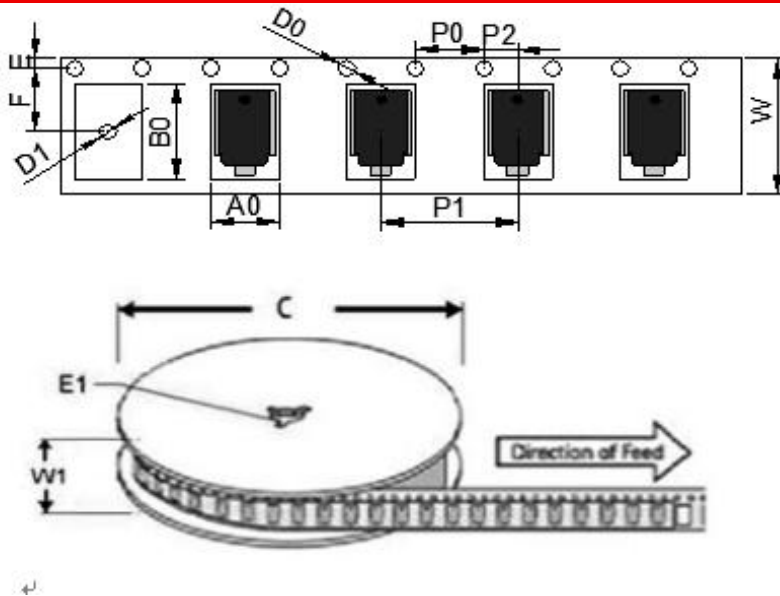
**Marking Diagram**



SM8T20A  
XXXX

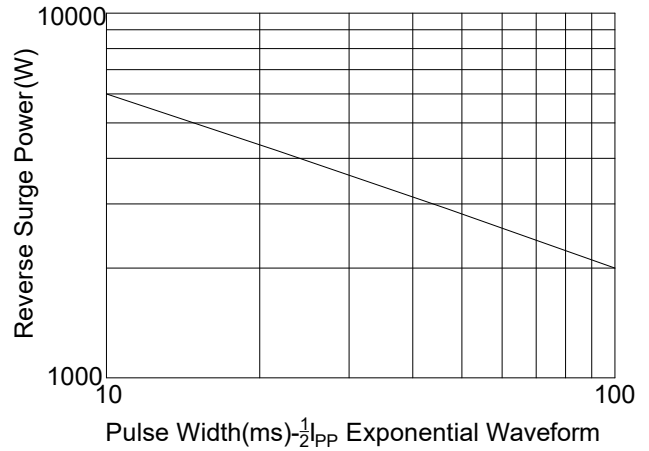
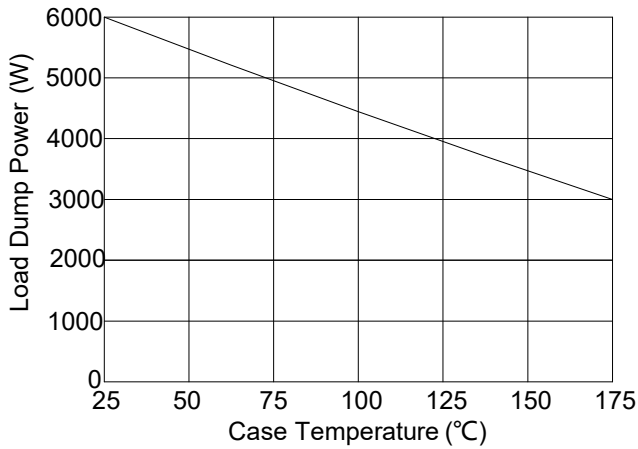
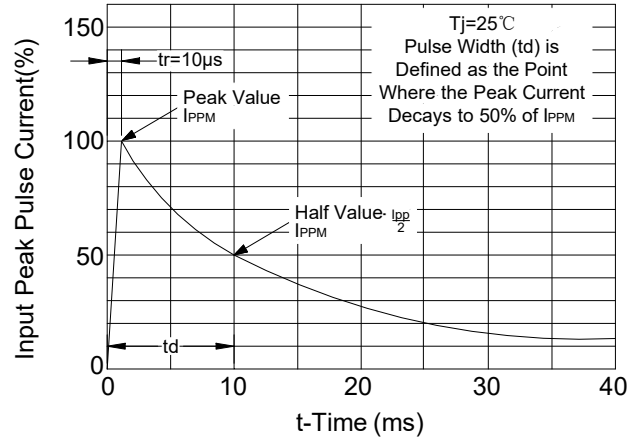
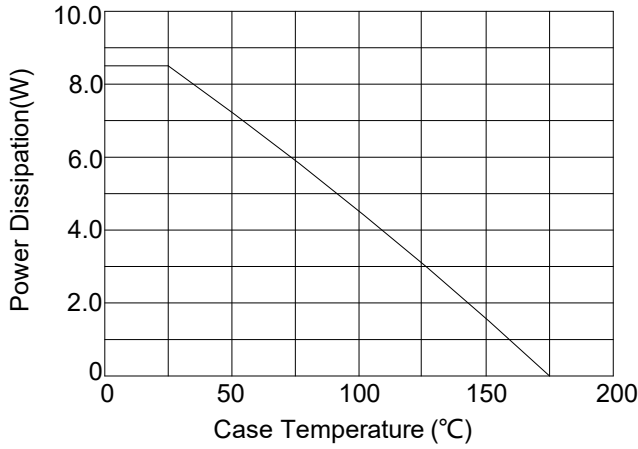
= Part Name  
= Date Code

**Carrier Tape Specification DO-218AB**



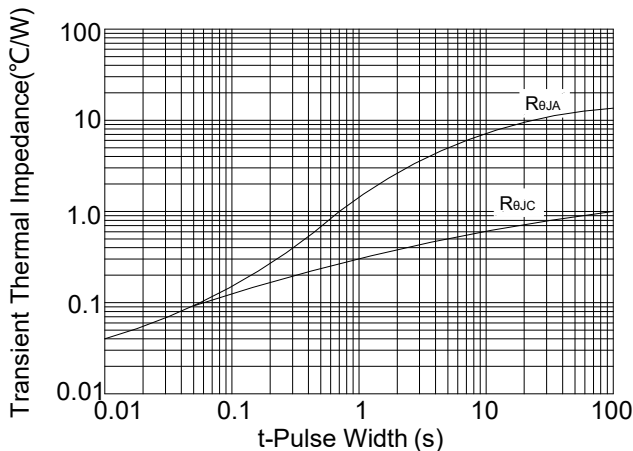
Ref.	Dimensions	
	Millimeters	Inches
A0	10.80 ± 0.3	0.425± 0.012
B0	16.13 ± 0.3	0.635 ± 0.012
C	330.0 ± 0.3	13.0 ± 0.012
D0	1.55 ± 0.2	0.061 ± 0.008
D1	1.55 ± 0.2	0.061± 0.008
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.30 ± 0.2	0.524 ± 0.008
F	11.50 ± 0.2	0.453 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	16.00 ± 0.2	0.630 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	24.00 ± 0.2	0.945 ± 0.008
W1	25.85 ± 0.2	1.018 ± 0.008

**Ratings and Characteristics Curves**



**FIG.3: Load Dump Power Characteristics (10ms Exponential Waveform)**

**FIG.4: Reverse Power Capability**



**FIG.5: Typical Transient Thermal Impedance**

**Technical Data  
Data Sheet N2146, Rev. -**



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